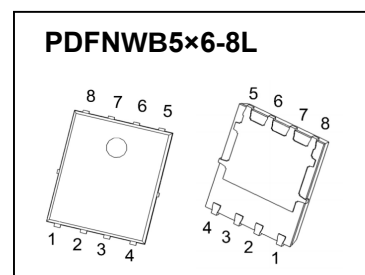




PDFNWB5×6-8L Plastic-Encapsulate MOSFETS

CJAC70SN15 N-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
150V	10mΩ@10V	70A



DESCRIPTION

The CJAC70SN15 uses shielded gate trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications

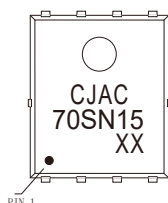
FEATURES

- High Power and current handing capability
- Load switch
- High density cell design for ultra low $R_{DS(ON)}$
- Lead free product is acquired
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

APPLICATIONS

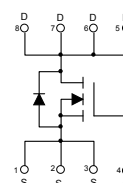
- SMPS and general purpose applications
- Hard switched and high frequency circuits
- Uninterruptible Power Supply
- Power management

MARKING



CJAC70SN15 = Part No.
Solid dot=Pin1 indicator.
XX=Date Code.

EQUIVALENT CIRCUIT



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	150	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	$I_D^{(1)}$	70	A
Pulsed Drain Current	$I_{DM}^{(2)}$	250	A
Single Pulsed Avalanche Energy	$E_{AS}^{(3)}$	320	mJ
Power Dissipation	$P_D^{(1)}$	114	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}^{(6)}$	62.5	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case	$R_{\theta JC}^{(1)}$	1.1	$^\circ\text{C/W}$
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	150			V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	2.8	4.0	V
Drain-source on-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 20A$		10	12	m Ω
Gate resistance	R_G	$f = 1MHz$		3.5		Ω
Dynamic characteristics ④ ⑤						
Total gate charge	Q_g	$V_{DS} = 75V, V_{GS} = 10V, I_D = 20A$		45	98	nC
Gate-source charge	Q_{gs}			10	25	
Gate-drain charge	Q_{gd}			5	12	
Input Capacitance	C_{iss}	$V_{DS} = 75V, V_{GS} = 0V, f = 100kHz$		3850	5800	pF
Output Capacitance	C_{oss}			252	430	
Reverse Transfer Capacitance	C_{rss}			7.5	13.5	
SWITCHING PARAMETERS ④ ⑤						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 75V,$ $R_G = 10\Omega, I_D = 20A$		19		ns
Turn-on rise time	t_r			9		
Turn-off delay time	$t_{d(off)}$			29		
Turn-off fall time	t_f			11		
Source-Drain Diode characteristics						
Body diode voltage	V_{SD} ④	$I_S = 20A, V_{GS} = 0V$			1.3	V
Reverse recovery time	T_{rr}	$V_R = 75V, I_F = 20A, di_F/dt = 100 A/\mu s$		85		ns
Reverse recovery charge	Q_{rr}			165		nC

Notes:

1. $T_C = 25^\circ\text{C}$ Limited only by maximum temperature allowed.

2. $P_W \leq 10\mu s$, Duty cycle $\leq 1\%$.

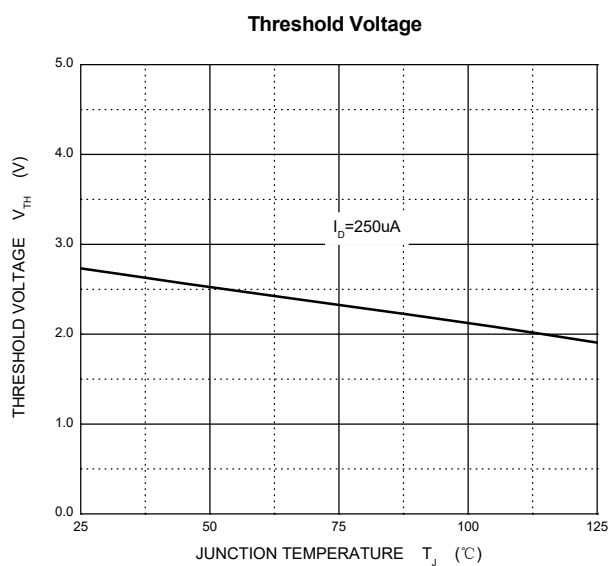
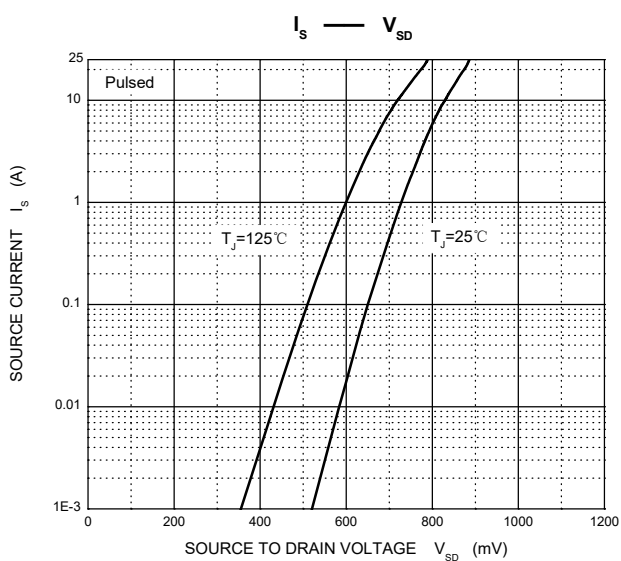
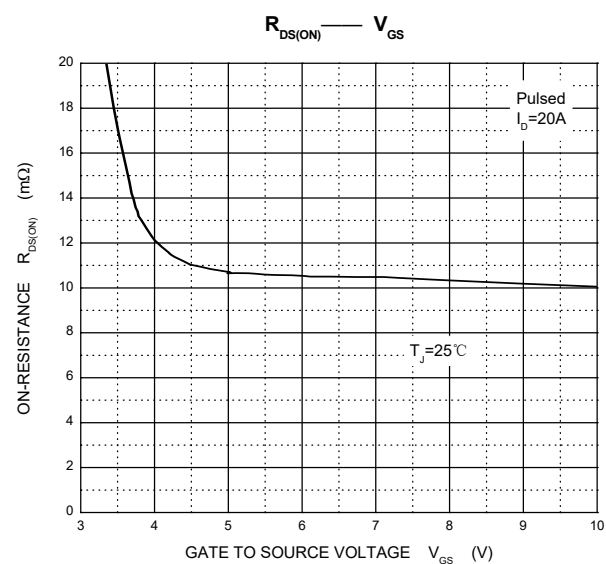
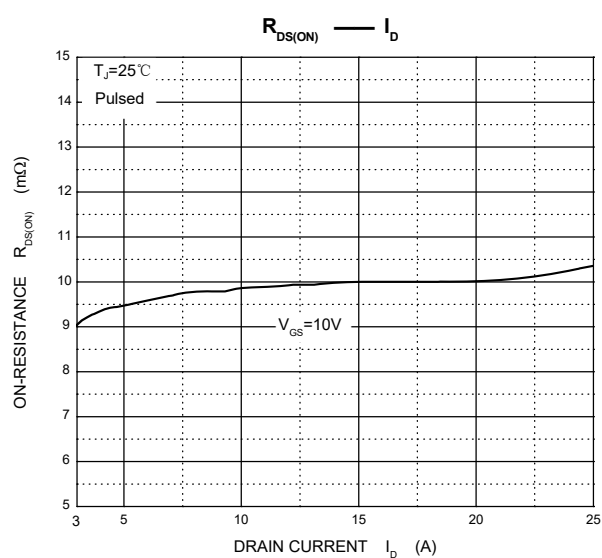
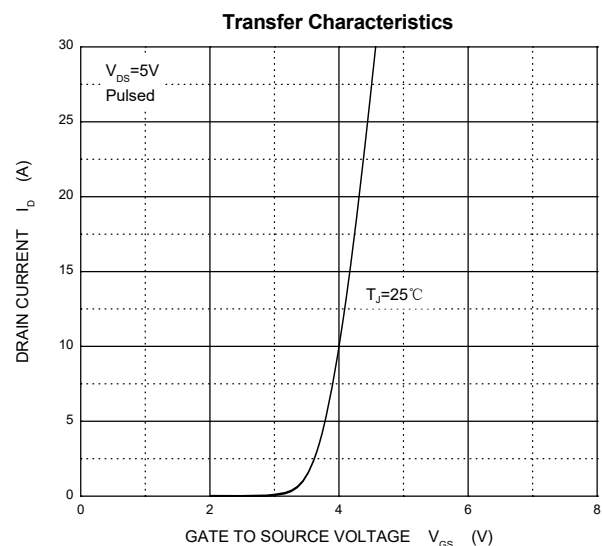
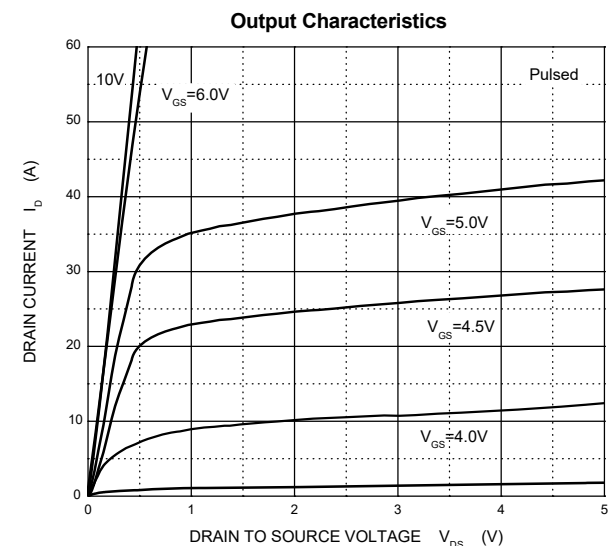
3. EAS condition: $V_{DD} = 50V, V_{GS} = 10V, L = 0.1mH, R_g = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.

4. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.

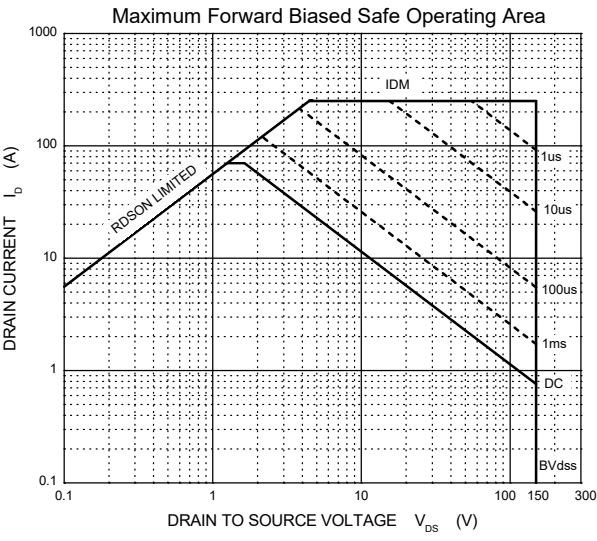
5. Guaranteed by design, not subject to production.

6. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_a = 25^\circ\text{C}$.

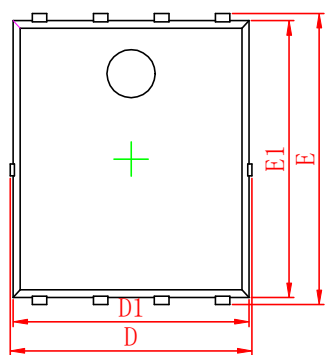
Typical Characteristics



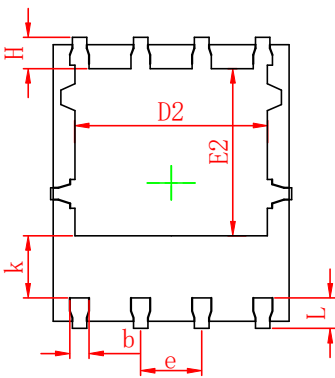
Typical Characteristics



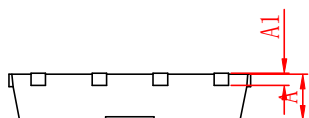
PDFNWB5×6-8L PACKAGE OUTLINE DIMENSIONS



Top View
[顶视图]



Bottom View
[背视图]

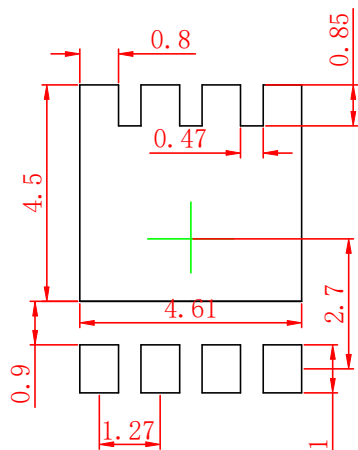


Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.90	1.10	0.035	0.043
A1	0.25 REF.		0.010 REF.	
D	4.90	5.10	0.193	0.201
D1	4.80	5.00	0.189	0.197
D2	3.90	4.10	0.154	0.161
E	5.90	6.10	0.232	0.240
E1	5.65	5.85	0.222	0.230
E2	3.35	3.65	0.132	0.144
k	1.20	1.50	0.047	0.059
b	0.20	0.45	0.008	0.018
e	1.27 BSC		0.050 BSC	
L	0.55	0.75	0.022	0.030
H	0.45	0.75	0.018	0.030

- Notes:
- 1 Dimensions exclusive of mold gate burrs.
 - 2 Dimensions exclusive of mold flash and cutting burrs.

PDFNWB5×6-8L Suggested Pad Layout

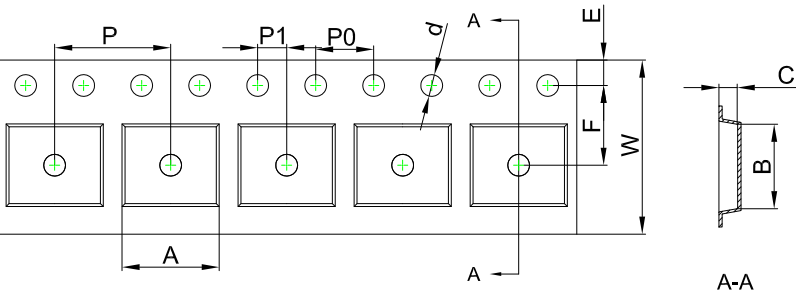


- Notes:
- 1 Controlling dimension: in millimeters.
 - 2 General tolerance:±0.05mm.
 - 3 The pad layout is for reference purpose only.

NOTICE

JSCJ reservesthe right to make modifications,enhancements,improvements,corrections or other changes without further notice to any product herein.JSCJ does not assume any liability arising out of the application or use of any product described herein.

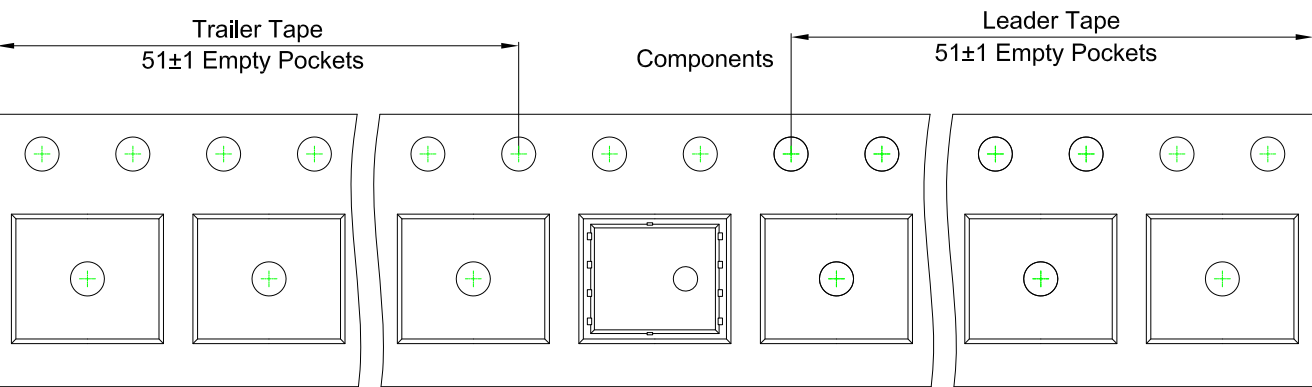
PDFNWB5×6-8L Embossed Carrier Tape



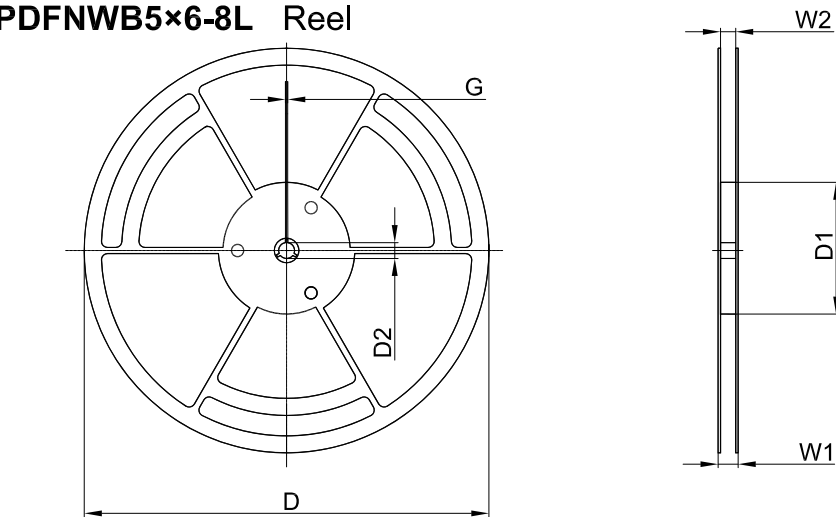
Packaging Description:
PDFNWB5×6-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 5,000 units per 13" or 33.0 cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
PDFNWB5×6-8L	6.30	5.30	1.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFNWB5×6-8L Tape Leader and Trailer



PDFNWB5×6-8L Reel



Dimensions are in millimeter						
Reel Option	D	D1	D2	G	W1	W2
13"Dia	Ø330.00	100.00	13.00	1.90	17.60	12.40

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
5,000 pcs	13 inch	5,000 pcs	340×336×29	50,000 pcs	353×346×365